Glow Discharge Proc

SPUTTERING AND PLASMA ETCHING

Brian Chapman

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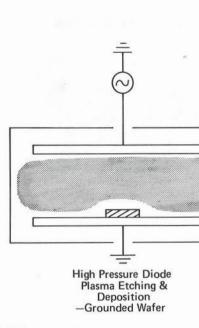
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Figure 7-23. High pressure diode plasma etching and dep

quarter of the applied rf peak-to-peak voltage (Chapter - 250 V for practical plasma etching processes. This is o measurements and by observation of the dark spaces for energy of ion bombardment on an electrode is determin and by collisions in the sheath, as discussed in Chapters

Reactive ion etching systems (Figure 7-24) are essenti systems. In sputtering, intense ion bombardment at the nowhere else. This is achieved by making the target area of the grounded chamber and baseplate. As a result, the very small, but the sheath at the target, and hence at the rf peak-to-peak, amounting typically to -300 V.

The different operating pressures of the two diode sys ence ion bombardment energies very greatly, because th collisions per unit length at the higher pressure is offset much thinner dark space sheath. The two effects would

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